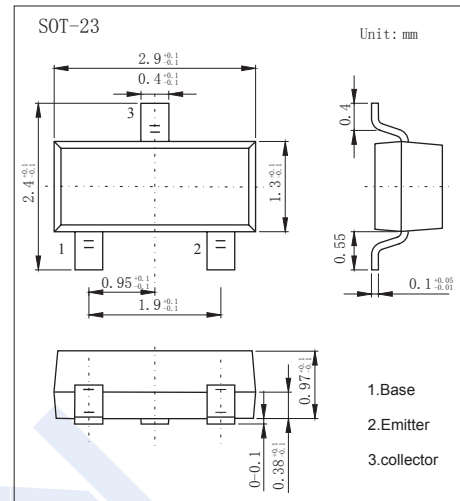


PNP Transistors

FMMT717

■ Features

- Collector Current Capability $I_C = -2.5A$
- Collector Emitter Voltage $V_{CE0} = -12V$
- Complementary to FMMT617

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-12	V
Collector - Emitter Voltage	V_{CE0}	-12	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-2.5	A
Collector Current - Pulse	I_{CP}	-10	
Base Current	I_B	-0.5	
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

PNP Transistors

FM717

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = -100 μA, I _E =0	-12			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -10 mA, I _B =0	-12			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -10 V, I _E =0			-100	nA
Collector- emittercut-off current	I _{CES}	V _{CE} = -10 V, I _E =0			-100	
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100 mA, I _B =-10mA			-17	mV
		I _C =-1 A, I _B =-10mA			-140	
		I _C =-1.5 A, I _B =-50mA			-170	
		I _C =-2.5 A, I _B =-50mA			-220	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-2.5 A, I _B =-50mA			-1	V
Base - emitter turn-on voltage	V _{BE(on)}	V _{CE} = -2V, I _C = -2.5A			-1	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -10mA	300			
		V _{CE} = -2V, I _C = -100mA	300			
		V _{CE} = -2V, I _C = -2.5A	180			
		V _{CE} = -2V, I _C = -8A	60			
		V _{CE} = -2V, I _C = -10A	45			
Turn-on time	t _{on}	V _{CC} =-6V, I _C =-2A		70		ns
Turn-off time	t _{off}	I _{B1} =I _{B2} =50mA		130		
Collector output capacitance	C _{ob}	V _{CB} = -10V, f=1MHz			30	pF
Transition frequency	f _r	V _{CE} = -10V, I _C = -50mA, f=100MHz	80			MHz

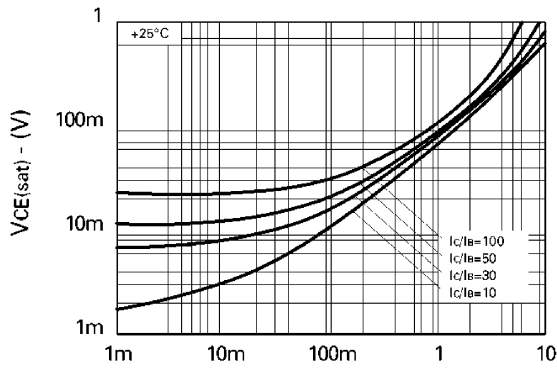
■ Marking

Marking	717
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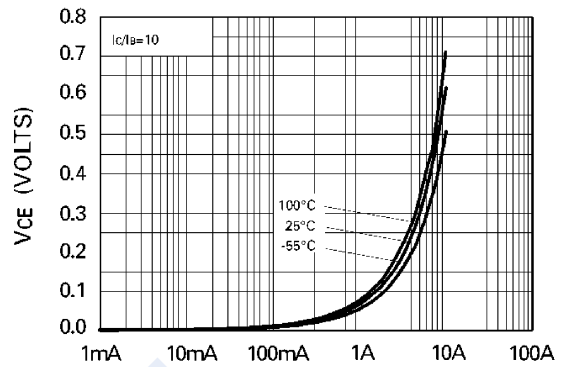
PNP Transistors

FM717

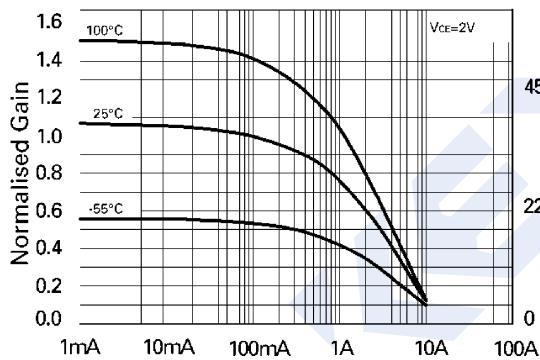
Typical Characteristics



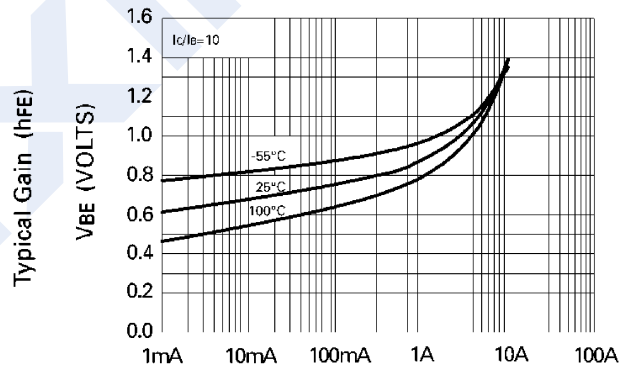
Collector Current (A)
VCE(SAT) vs IC



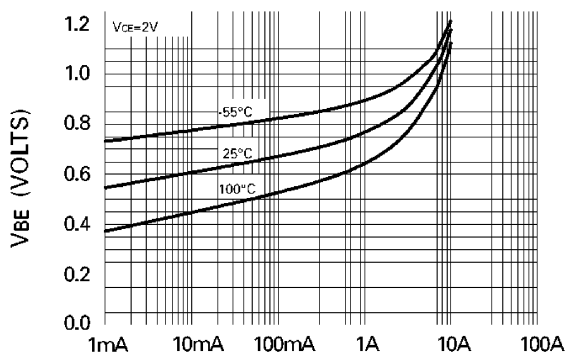
Collector Current
VCE(SAT) vs IC



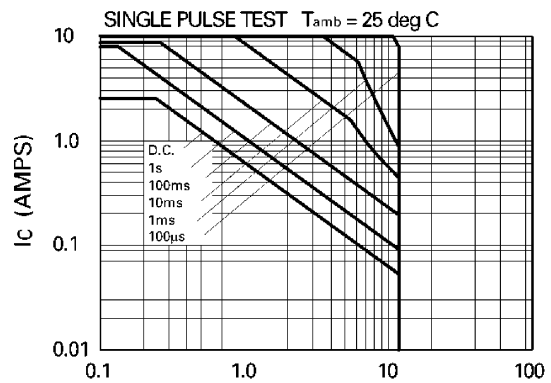
Collector Current
hFE vs IC



Collector Current
VBE(SAT) vs IC



Collector Current
VBE(ON) vs IC

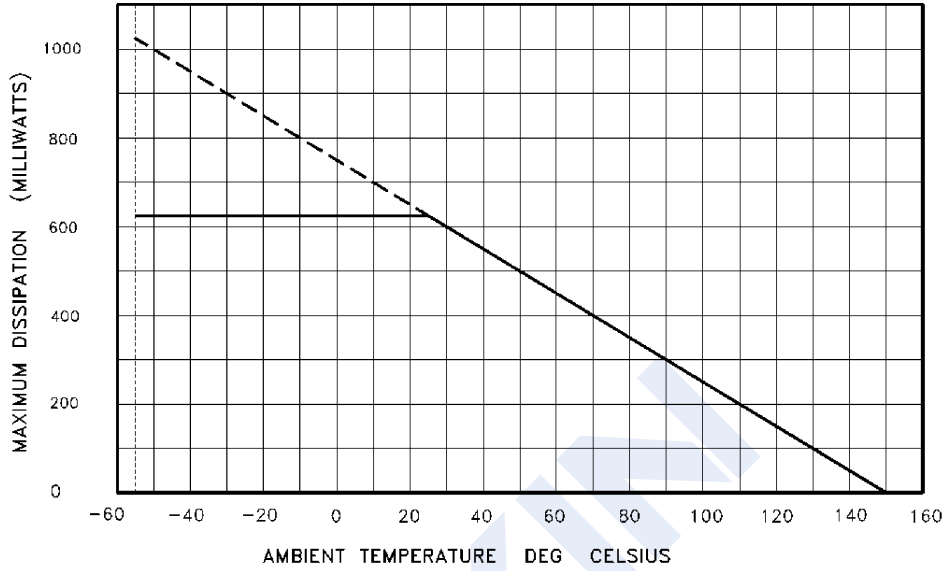


Safe Operating Area

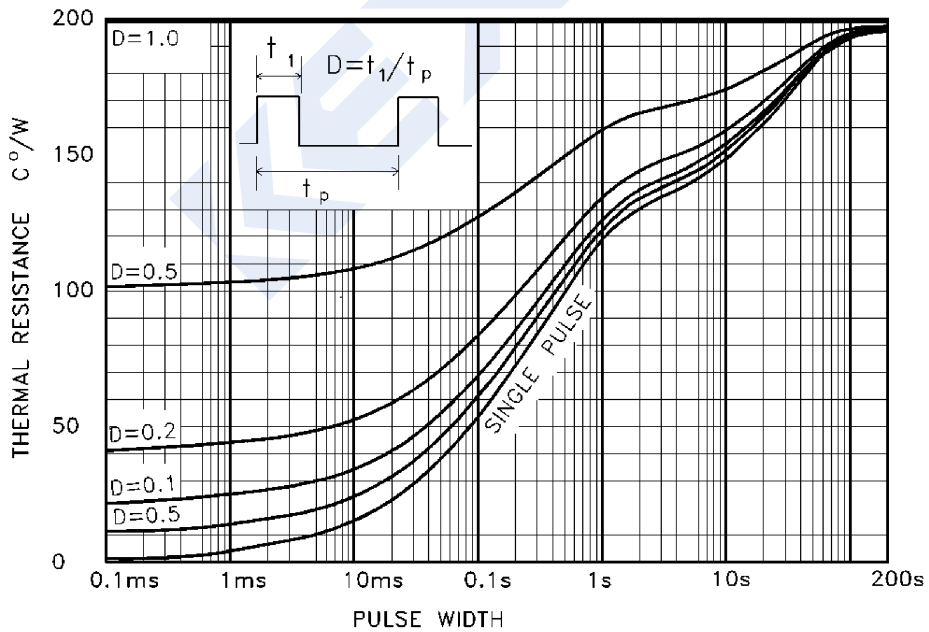
PNP Transistors

FM717

■ Typical Characteristics



DERATING CURVE



MAXIMUM TRANSIENT THERMAL RESISTANCE